

$$\phi_{B} = \phi (E_g, E_{Fd}, E_{F2})$$

$$= \phi (E_g, N_d, N_2)$$

$$N-1 \approx N \approx N + 1$$

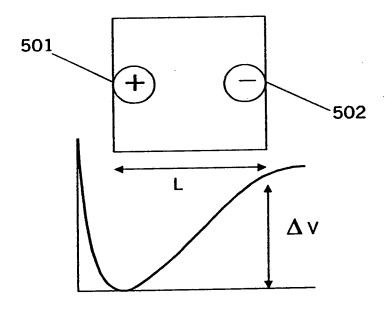
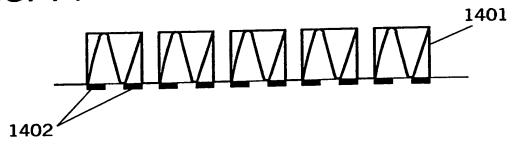


FIG. 5





Etc. Bipolar Cells | Oscillators | Sensors | Integrated Devices Molecular Structure of Semiconductor Material Atomic Level of Semiconductor Devices **Atomic Circuit Design** Macroscopic System Microscopic System

FIG. 2

FIG. 3

L,nm	Number of Si atoms	Sigle-dopant concentration, cm ⁻³	Equivalent resistivity, Ω – cm
100	50,000,000	1E+15	5.00
20	6,250,000	8E+15	2.00
10	50,000	1E+18	0.04
2	6,250	8E+18	0.01

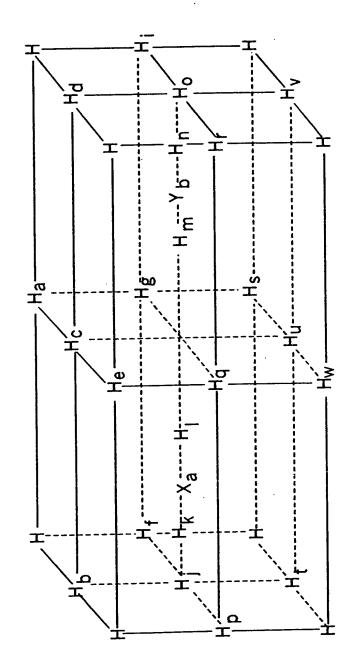


FIG. 4

-,Si⁹⁸ 98 8 Sim-Bb---S | 86 | 86 8 8 9 i a 8

FIG. 6

FIG. 7

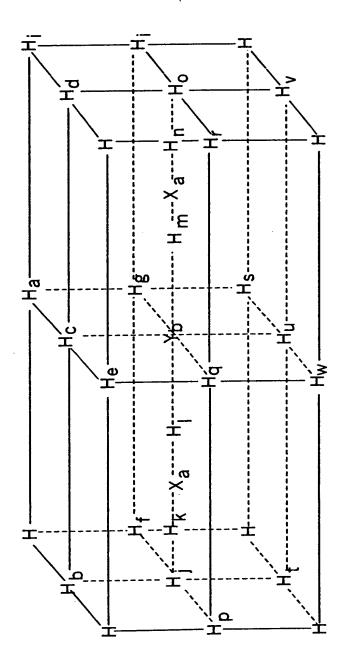


FIG. 8

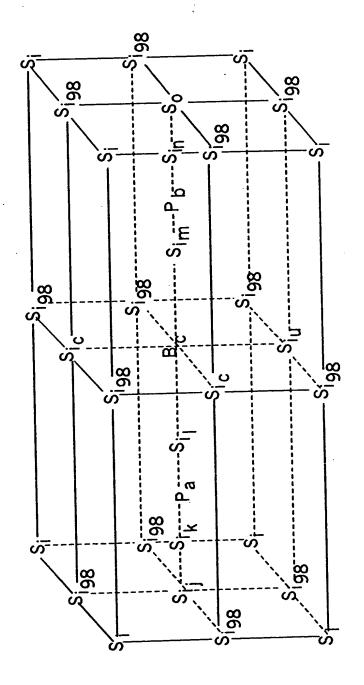


FIG. 9

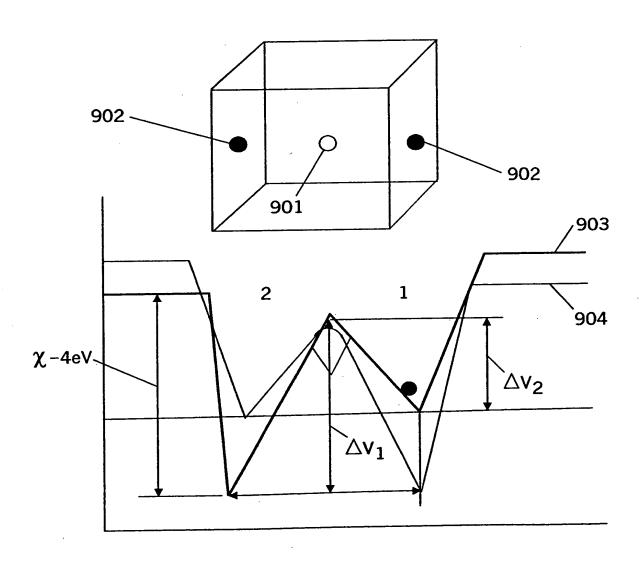


FIG. 10

$$\Delta V_1 = (e/\pi \epsilon_0 \epsilon) L^{-1}$$

$$\Delta V_2 = (e/2\pi \epsilon_0 \epsilon) L^{-1}$$

$$\Delta V_2 = \frac{1}{2} \Delta V_1$$

$$kT_{th} \sim \Delta V_2$$

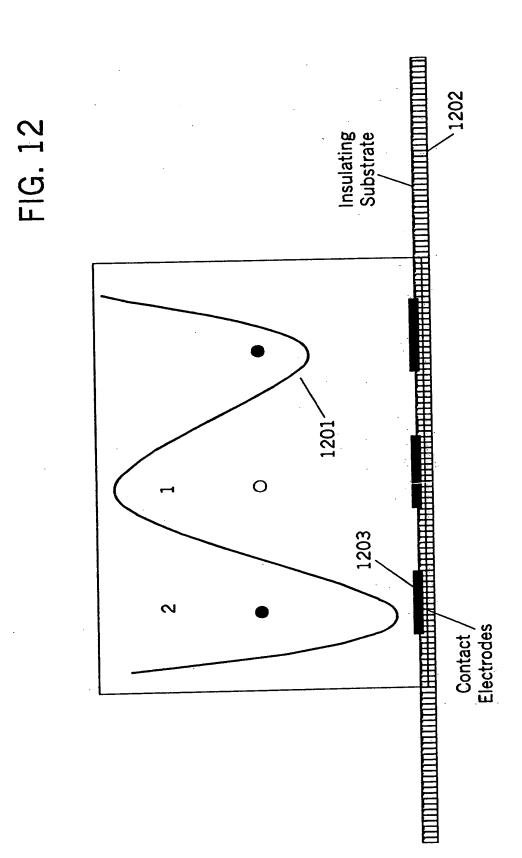
$$T_{th} \sim \Delta V_2/k$$

- Thermal Threshold

L, nm	ΔV ₁ Volts	ΔV ₂ Volts	т _{th} ,К
100	0.012	0.006	50
50	0.023	0.012	100
40	0.030	0.015	150
30	0.040	0.020	200
20	0.060	0.030	300
10	0.120	0.060	600
5	0.230	0.120	1200

FG. 1

£	۵۷1	۵۷2	; :	S	f.GH2	Power/cell,	Power/cm ² ,	Power/cell, Power/cm2, Power/1D array
<u> </u>	Volts	Volts	th,,,			>	W/cm ²	w/cm
100	0.012	900'0	50	50 3.14E-10	3.18	5.86E-12	0.0586	2.93E.07
50	0.023	0.012	100	100 1.11E-10	8.99	3.31E-11	1.33	3.31E.06
40	0.03	0.015	150	150 7.96E-11	12.6	5.79E-11	3.62	7.24E-06
30	0.04	0.020	200	200 5.17E-11	19.4	1.19E-10	13.2	1.98E.05
20	90.0	0:030	300	300 2.81E-11	35.6	3.28E·10	81.9	8.19E-05
10	0.12	090.0	900	600 9.94E-12	101	1.85E-09	1850.0	9.26E-04
2	0.23	0.120	1200	1200 3.52E-12	284	1.05E-08	41900.0	1.05E-02



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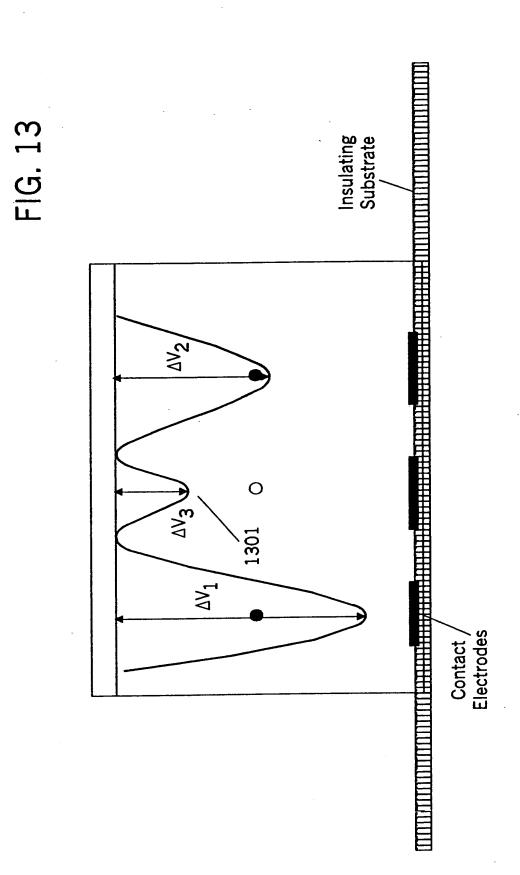


FIG. 15

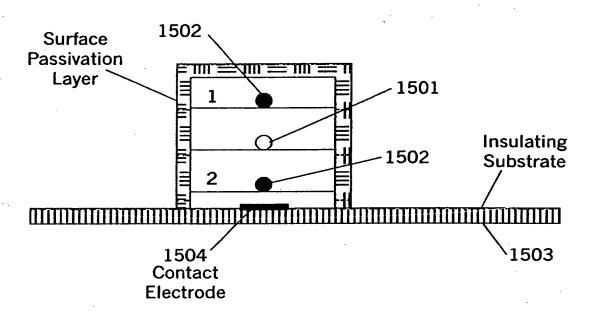


FIG. 16

